VCRR P-ChannelEnhancement Mode Power MOSFET

Description

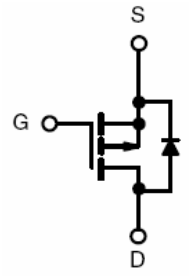
The VCRR60P82AD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

- V_{DS} =-60V,I_D =-82A
  $R_{DS(ON)}$ <13mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ <16mΩ @ V_{GS}=-4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Load switch



Schematic diagram

Marking and pin assignment

TO-263-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package
VCRR60P82AD		TO-263-2L

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-82	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	-58	A
Pulsed Drain Current	I_{DM}	-328	A
Maximum Power Dissipation	P_D	150	W
Derating factor		1.0	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	722	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance, Junction-to-Case(Note 2)	$R_{\theta JC}$	1.0	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

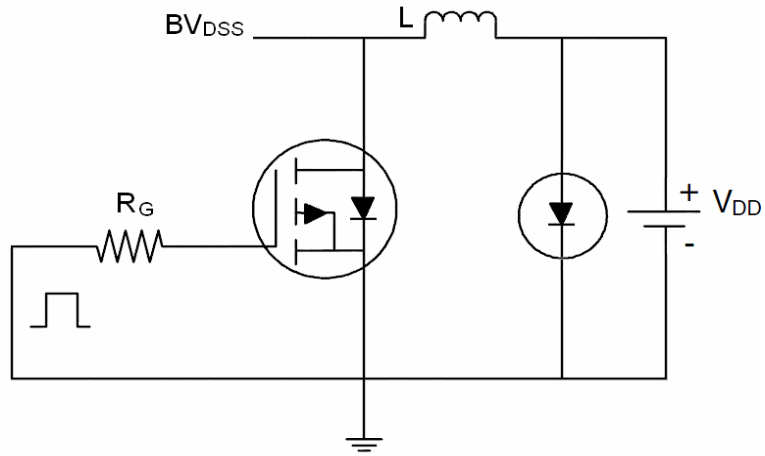
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.2	-1.8	-2.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-20A	-	11	13	mΩ
		V_{GS}=-4.5V, I_D=-20A	-	13	16	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-20A	-	25	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-30V,V_{GS}=0V, F=1.0MHz	-	5604	-	PF
Output Capacitance	C_{oss}		-	356	-	PF
Reverse Transfer Capacitance	C_{rss}		-	265	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-30V, R_L=1.5Ω, V_{GS}=-10V,R_G=3Ω	-	18	-	nS
Turn-on Rise Time	t_r		-	20	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	55	-	nS
Turn-Off Fall Time	t_f		-	35	-	nS
Total Gate Charge	Q_g	V_{DS}=-30,I_D=-20A, V_{GS}=-10V	-	62.1		nC
Gate-Source Charge	Q_{gs}		-	9.3		nC
Gate-Drain Charge	Q_{gd}		-	16.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-20A	-		-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-82	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, I_F =-20A di/dt = -100A/μs (Note3)	-	49		nS
Reverse Recovery Charge	Qrr		-	71		nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

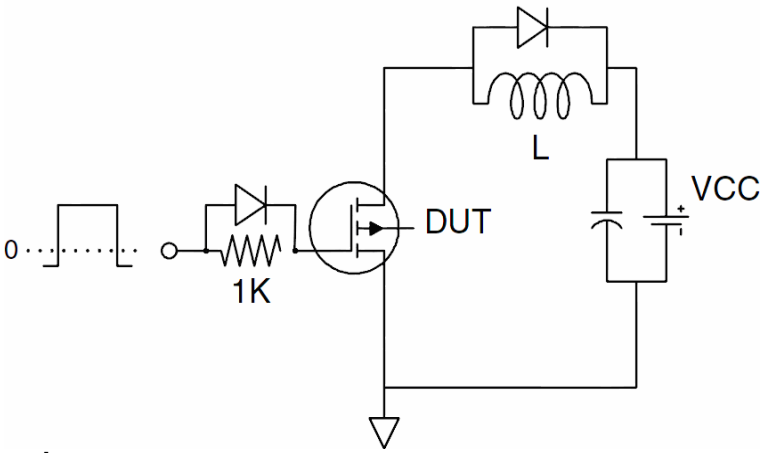
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: Tj=25℃,V_{DD}=-30V,V_G=-10V,L=0.5mH,Rg=25Ω

Test Circuit

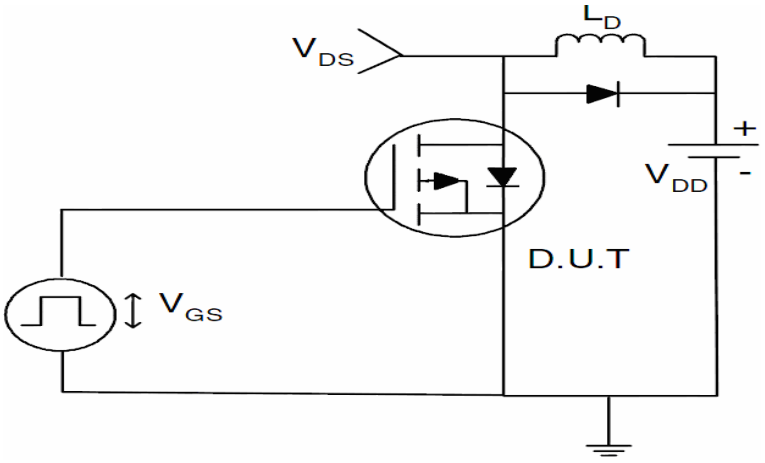
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

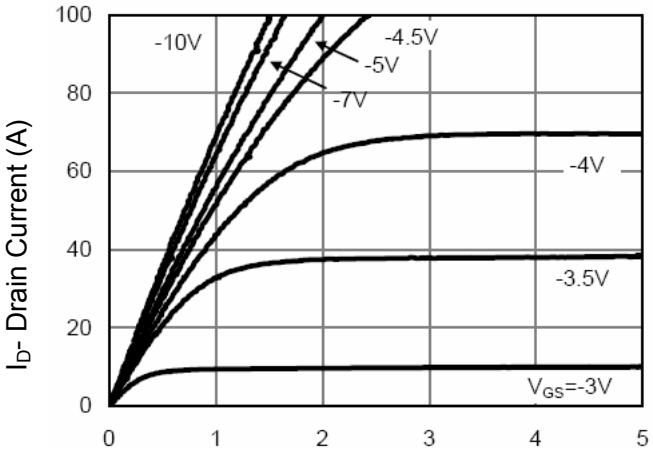


Figure 1 Output Characteristics

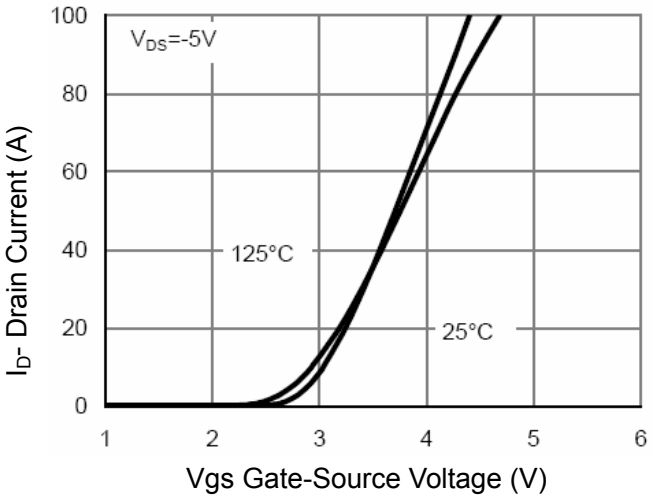


Figure 2 Transfer Characteristics

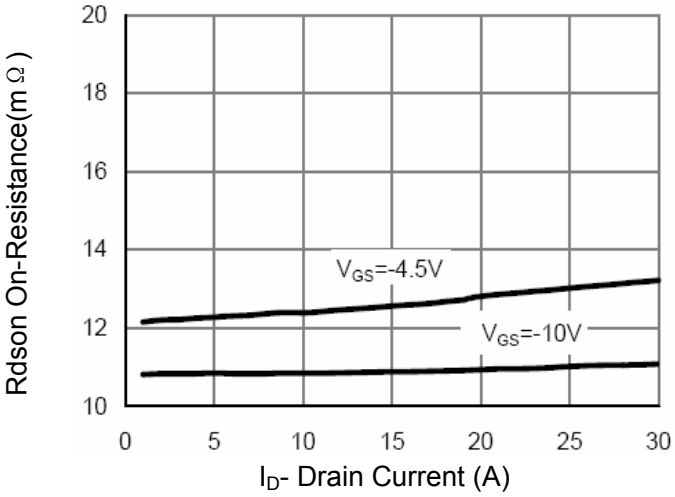


Figure 3 Rdson- Drain Current

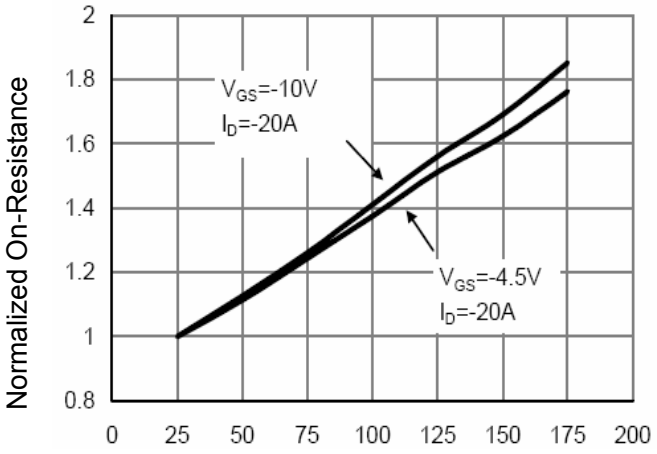


Figure 4 Rdson-Junction Temperature

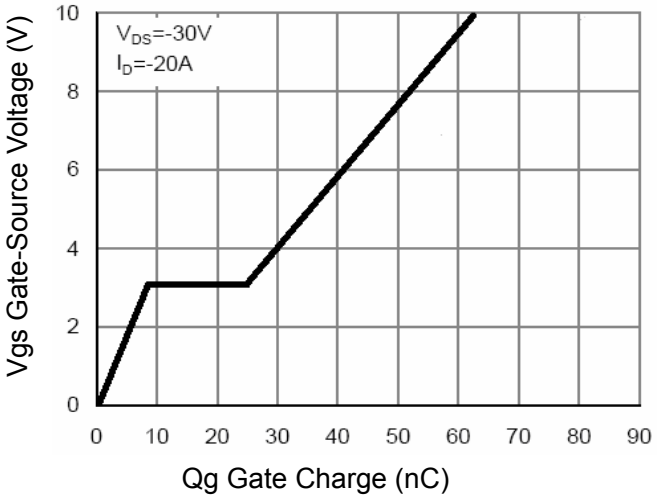


Figure 5 Gate Charge

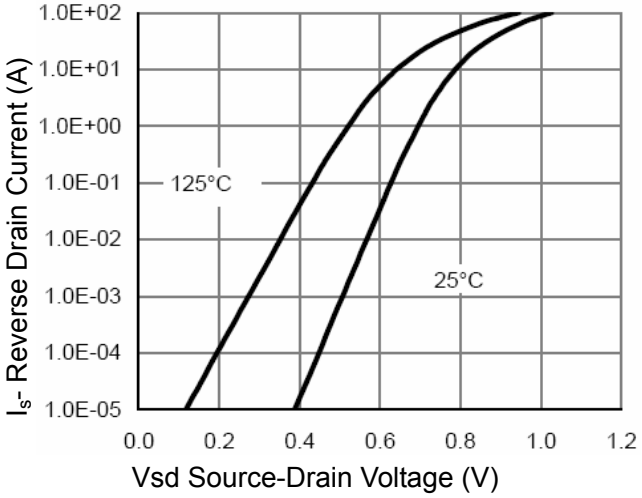


Figure 6 Source- Drain Diode Forward

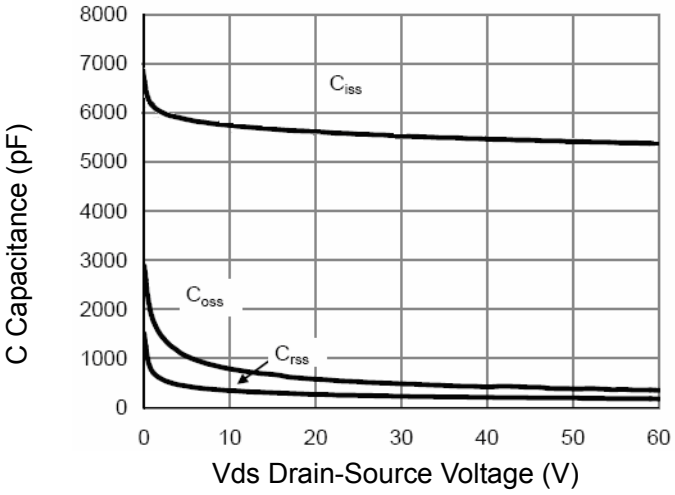


Figure 7 Capacitance vs Vds

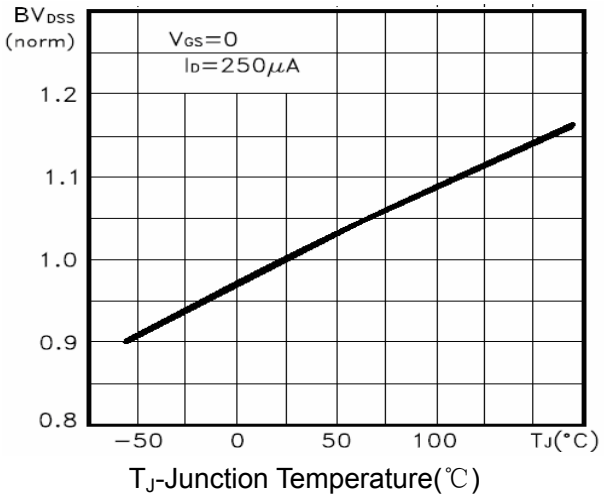


Figure 9 BV_{DSS} vs Junction Temperature

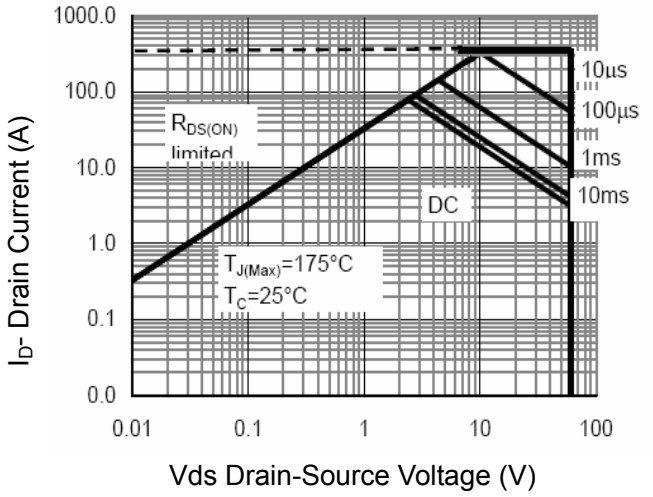


Figure 8 Safe Operation Area

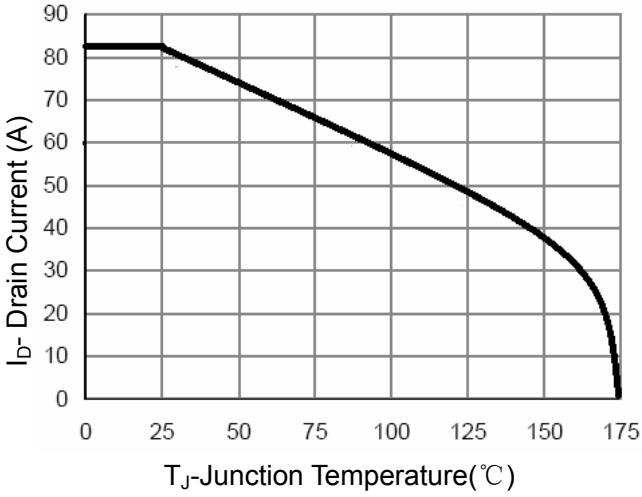


Figure 10 ID Current Derating vs Junction Temperature

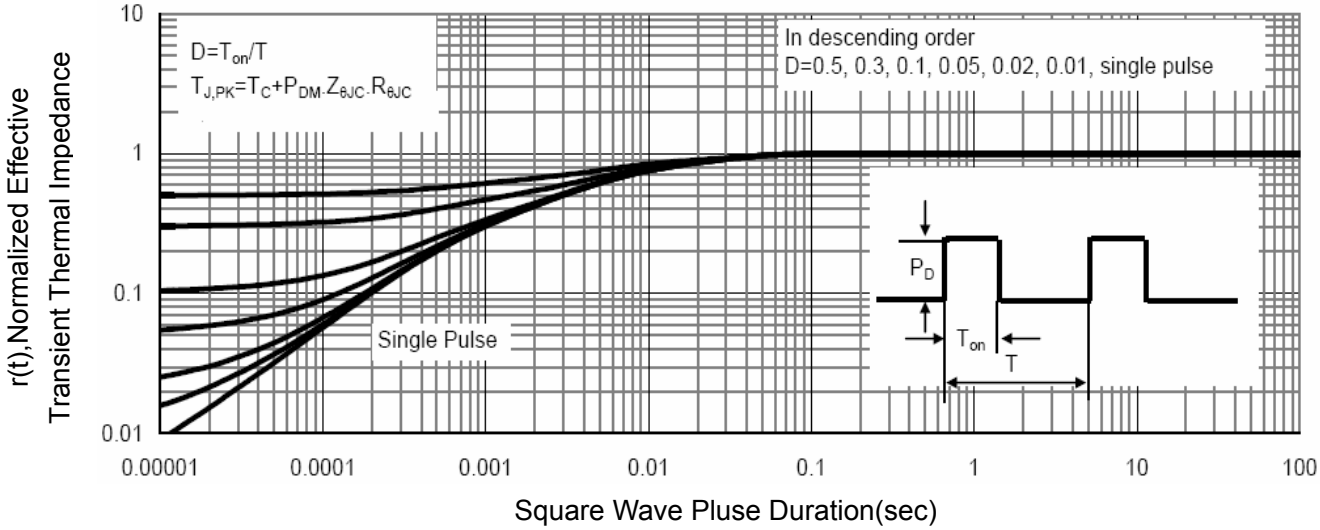
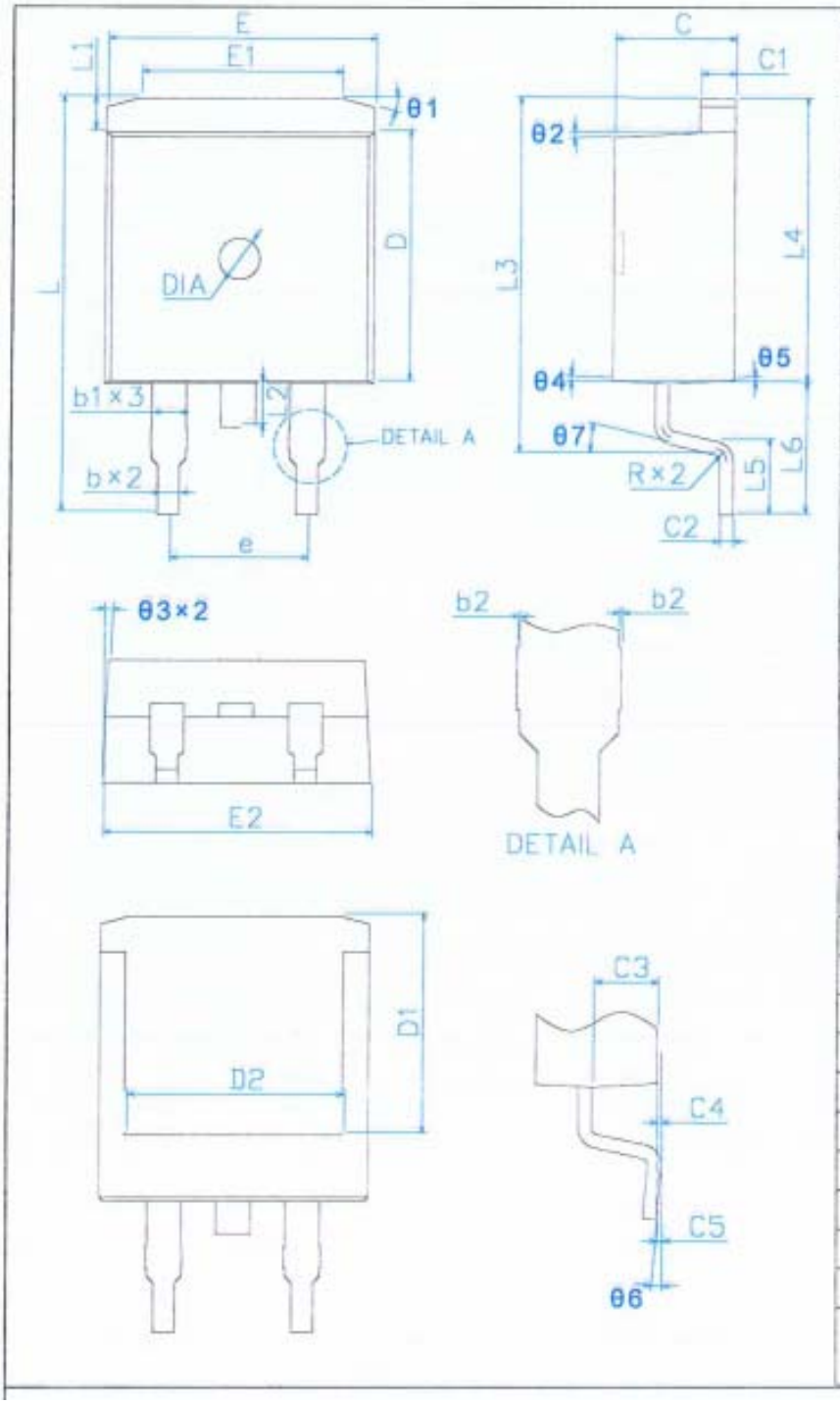


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



标注	尺寸(mm)
E	9.88±0.10
E1	7.40±0.20
E2	9.90±0.15
L	15.20±0.25
L1	1.30±0.15
L2	1.60±0.10
L3	13.00±0.20
L4	10.40±0.15
L5	2.40±0.15 (C5=0.25)
L6	4.80±0.20
b	0.80±0.07
b1	1.27±0.07
b2	0.05±0.07
C	4.48±0.10
C1	1.30±0.07
C2	0.50±0.07
C3	2.40±0.15
C4	0.10±0.08
C5	0.10±0.08
D	9.20±0.10
D1	8.00±0.10
D2	8.00±0.10
R	0.50±0.10
θ1	15° ±2°
θ2	3° ±2°
θ3	3° ±2°
θ4	3° ±2°
θ5	3° ±2°
θ6	0° ~5°
θ7	13° ±2°
e	5.08±0.10
DIA	宽 1.50±0.10 深 0.30±0.15

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